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(71) Applicant *(for all designated States except US)*: **PLASTIC LOGIC LIMITED** [GB/GB]; Sheraton House, Castle Park, Cambridge CB3 0AX (GB).

(72) Inventors; and

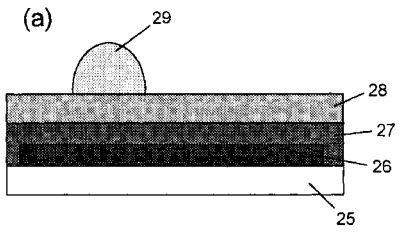
(75) Inventors/Applicants *(for US only)*: **SIRRINGHAUS, Henning** [DE/GB]; Churchill College, Cambridge CB3 0DS (GB). **FRIEND, Richard, Henry** [GB/GB]; 37 Barton Road, Cambridge CB3 9LG (GB). **KAWASE, Takeo** [JP/GB]; 18 Eachard Road, Cambridge CB3 6HY (GB).

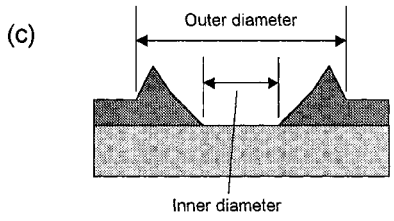
(74) Agents: **SLINGSBY, Philip, Roy** et al.; Page White & Farrer, 54 Doughty Street, London WC1N 2LS (GB).

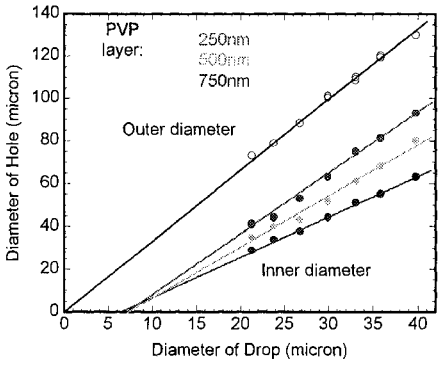
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(54) Title: FORMING INTERCONNECTS







(57) Abstract: A method for forming an electronic device, comprising: forming a first conductive or semiconductive layer; forming a sequence of at least one insulating layer and at least one semiconducting layer over the first conductive or semiconductive layer; locally depositing solvents at a localised region of the insulating layer so as to dissolve the sequence of insulating and semiconducting layers in the region to leave a void extending through the sequence of layers; and depositing conductive or semiconductive material in the void.

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